

1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

2. Features and benefits

- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- General purpose low power motor control
- General purpose switching and phase control

4. Quick reference data

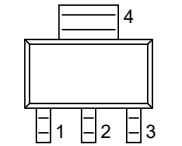
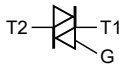
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{sp}} \leq 110\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	12.5	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 16.7\text{ ms}$	-	-	13.8	A
T_{j}	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G+; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	-	0.4	3	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G-; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	-	1.3	3	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G-; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	-	1.4	3	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G+; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	-	3.8	7	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 11		-	1.3	5	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; Fig. 12		-	1.2	1.5	V
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; R _{GT1(ext)} = 1 kΩ; Fig. 14		10	20	-	V/μs
dV _{com} /dt	rate of change of commutating voltage	V _D = 400 V; T _j = 125 °C; dI _{com} /dt = 0.5 A/ms; I _T = 1 A; gate open circuit		2	-	-	V/μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 SC-73 (SOT223)	 sym051
2	T2	main terminal 2		
3	G	gate		
4	T2	mainterminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT131W-600	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{sp}} \leq 110\text{ }^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4; Fig. 5		-	12.5	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$		-	13.8	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; SIN		-	0.78	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{G}} = 6\text{ mA}$		-	50	$\text{A}/\mu\text{s}$
				-	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 14\text{ mA}$		-	10	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 6\text{ mA}$		-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	$^{\circ}\text{C}$
T_{j}	junction temperature			-	125	$^{\circ}\text{C}$

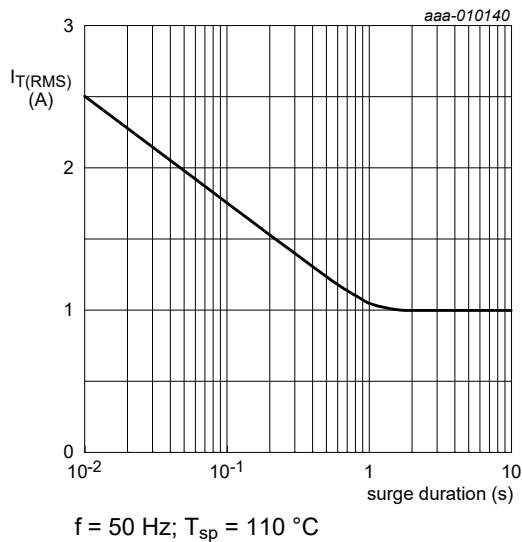


Fig. 1. RMS on-state current as a function of surge duration; maximum values

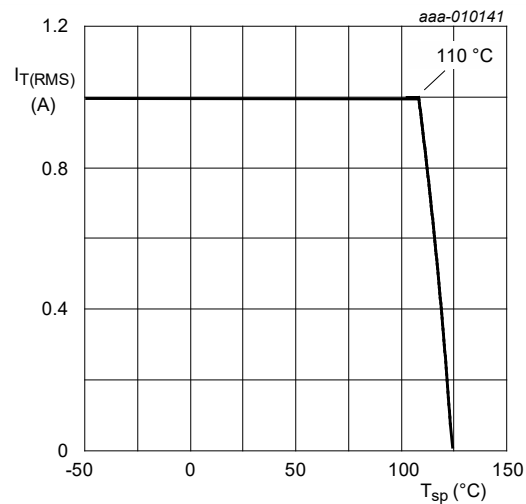
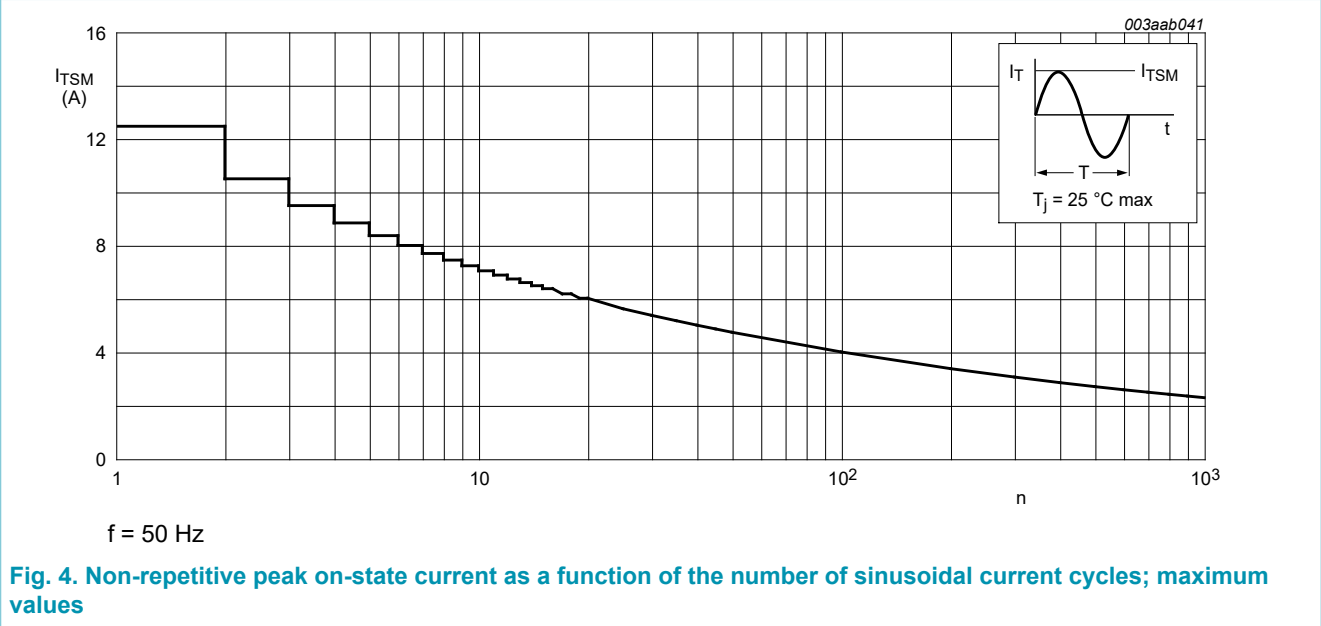
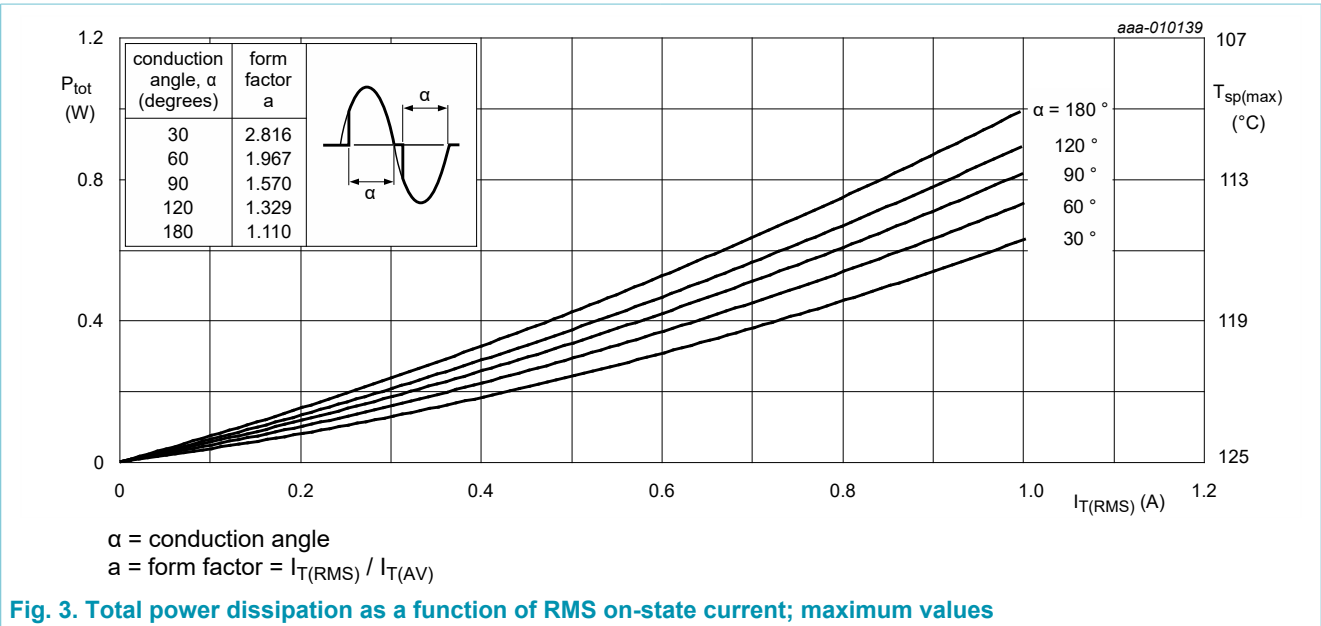
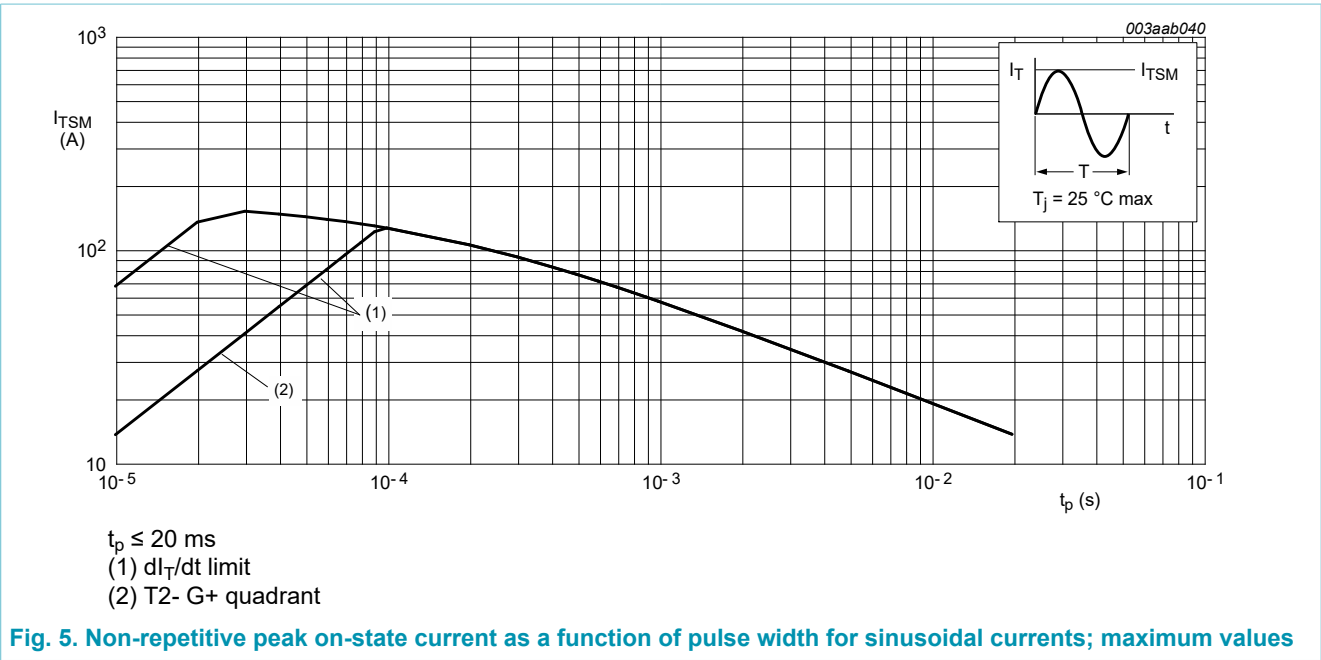


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

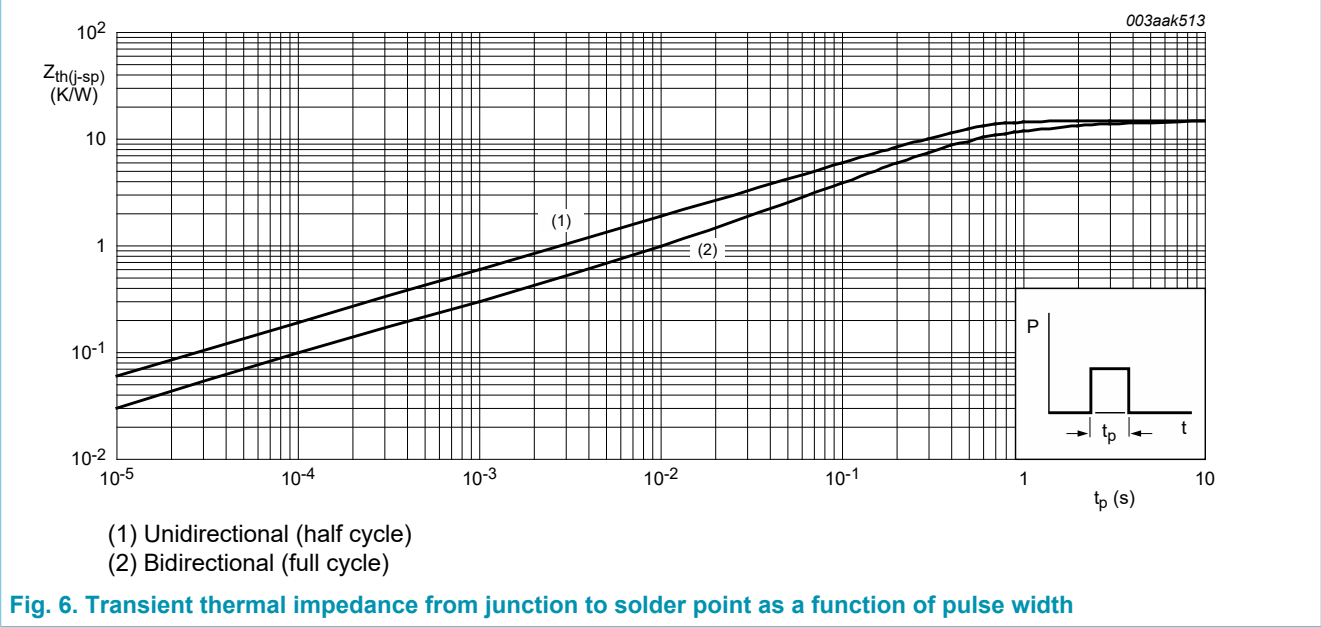


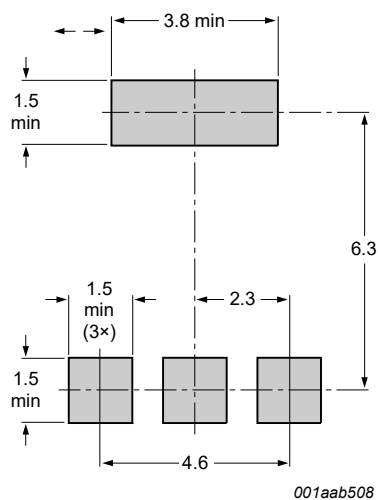


8. Thermal characteristics

Table 5. Thermal characteristics

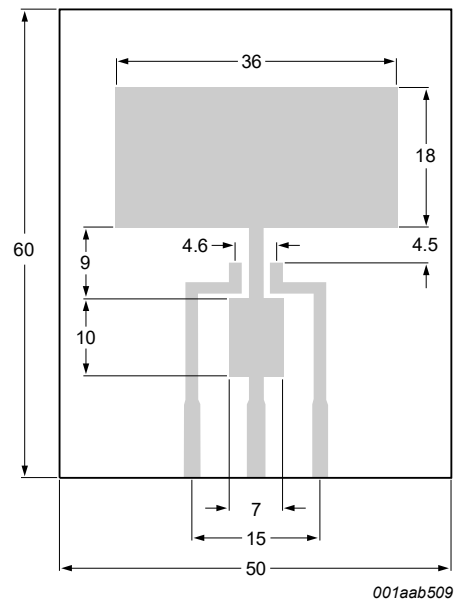
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air; printed circuit board mounted; minimum footprint; Fig. 7	-	156	-	K/W
		in free air; printed circuit board mounted; pad area; Fig. 8	-	70	-	K/W





All dimensions are in mm

Fig. 7. Minimum footprint SOT223



All dimensions are in mm

Printed circuit board:

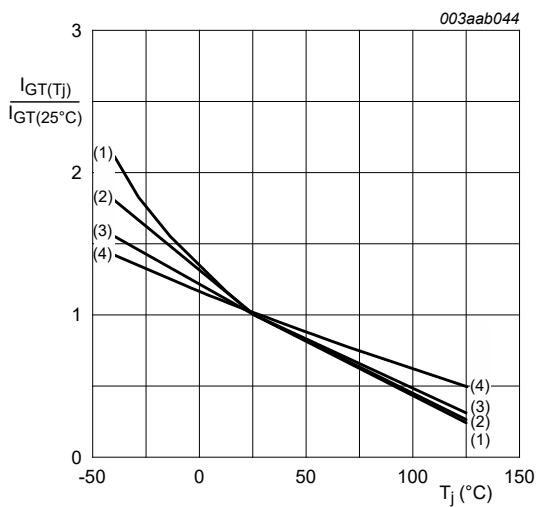
FR4 epoxy glass (1.6 mm thick), copper laminate (35 um thick)

Fig. 8. Printed circuit board pad area: SOT223

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	0.4	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	1.3	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	1.4	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	3.8	7	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.2	5	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	4	8	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1	5	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	2.5	8	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	1.3	5	mA
V_T	on-state voltage	$I_T = 1.4\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 12	-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 13	-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 13	0.2	0.3	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; $R_{GT1(ext)} = 1\text{ k}\Omega$; Fig. 14	10	20	-	V/ μs
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $dI_{com}/dt = 0.5\text{ A/ms}$; $I_T = 1\text{ A}$; gate open circuit	2	-	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 1.5\text{ A}$; $V_D = 600\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

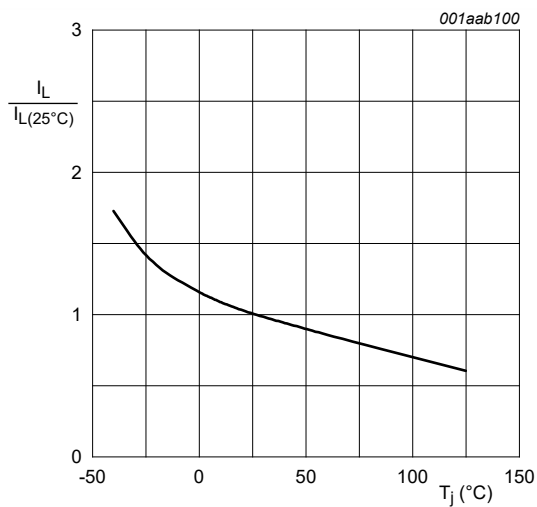


Fig. 10. Normalized latching current as a function of junction temperature

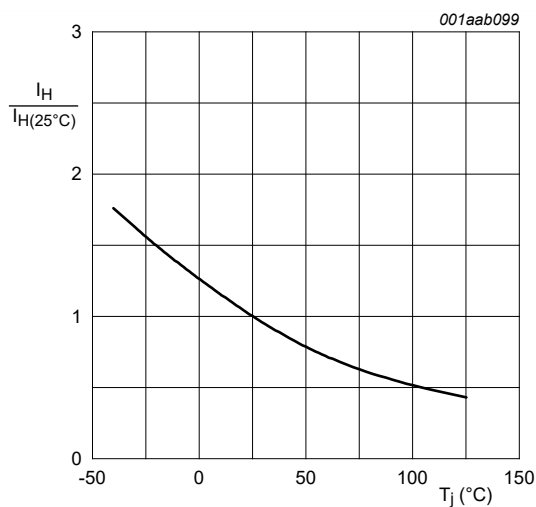
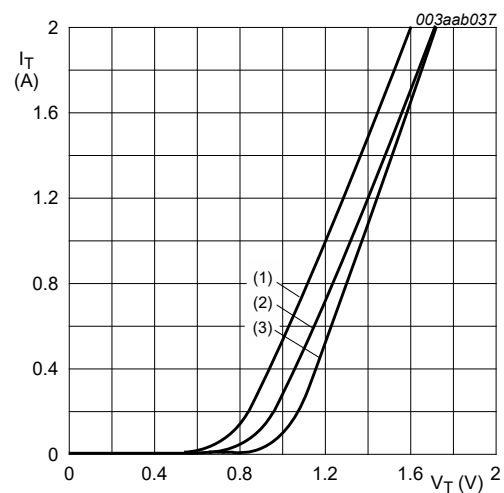


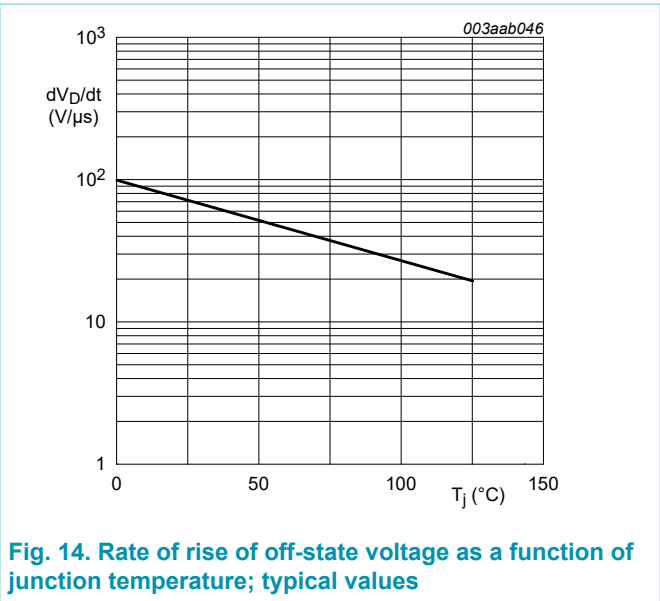
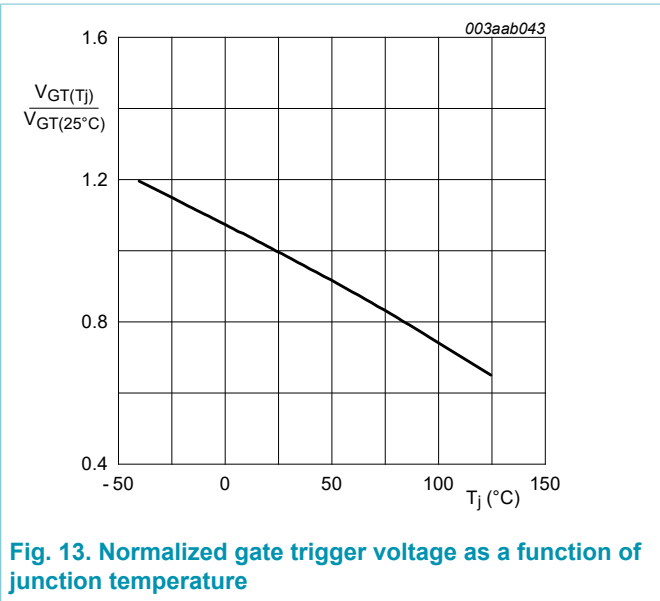
Fig. 11. Normalized holding current as a function of junction temperature



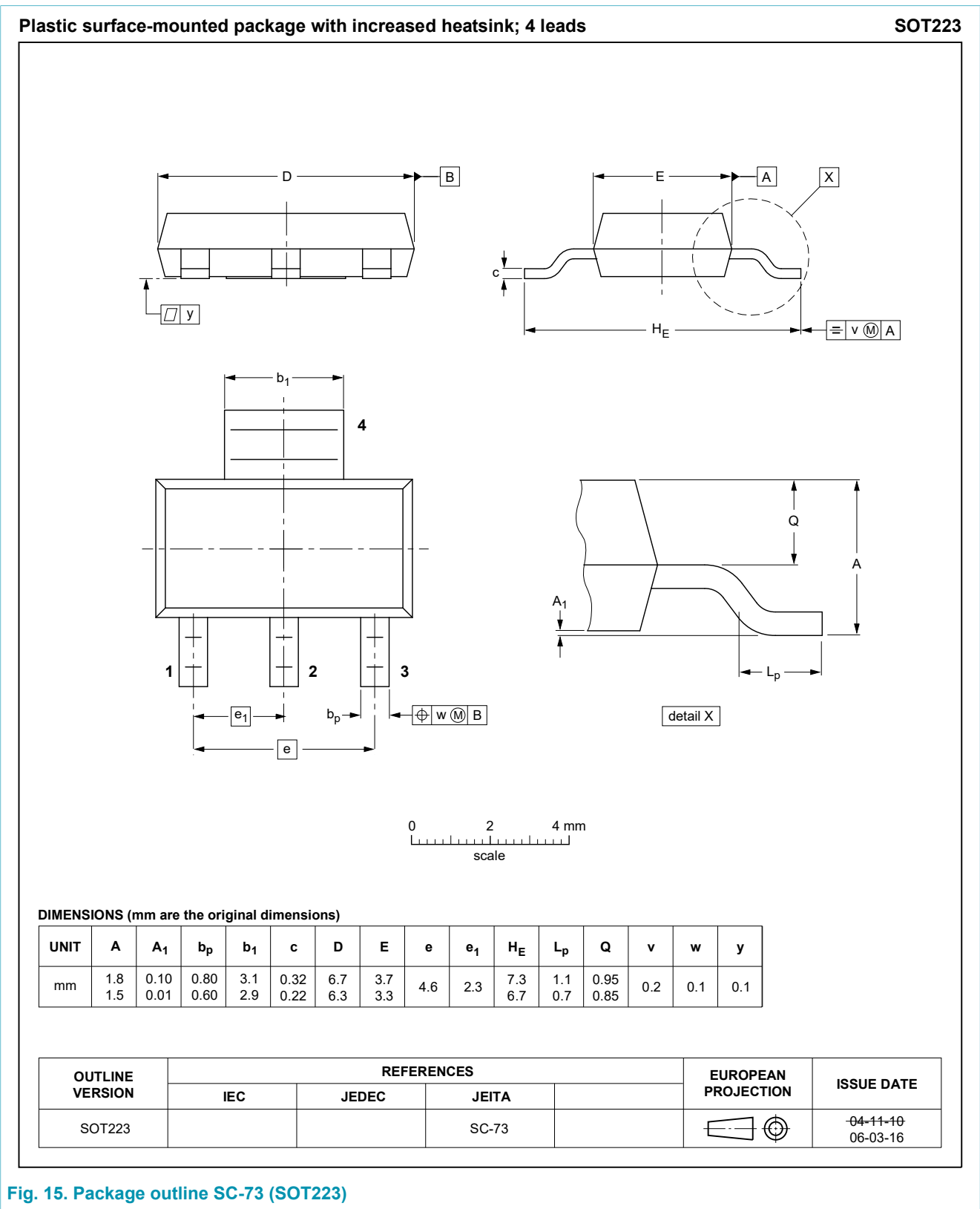
$V_o = 0.92 \text{ V}; R_s = 0.4 \Omega$

- (1) $T_j = 125^\circ\text{C}$; typical values
- (2) $T_j = 125^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

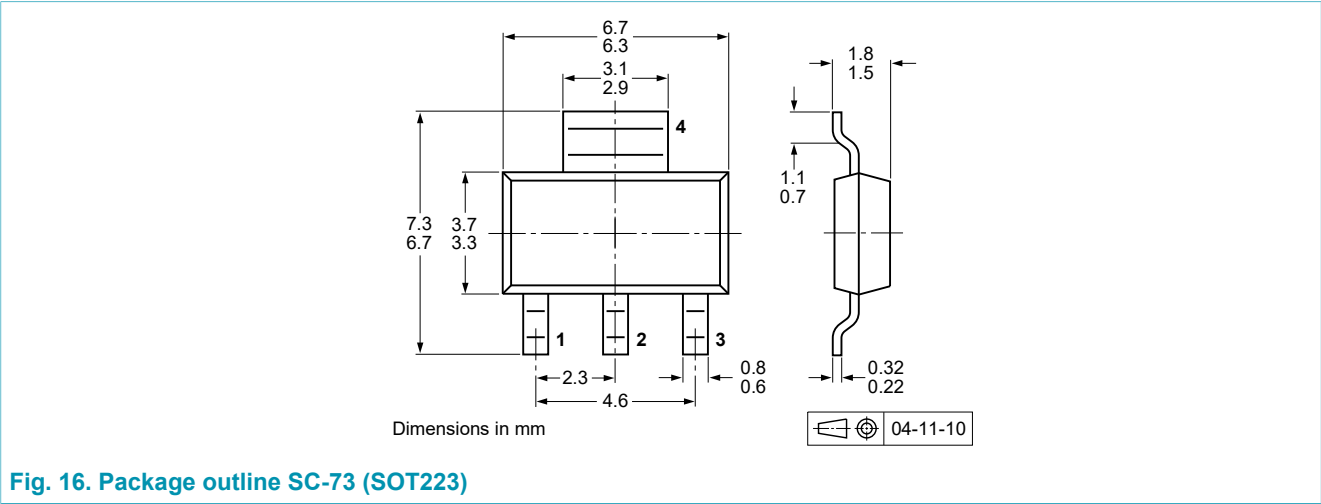
Fig. 12. On-state current as a function of on-state voltage



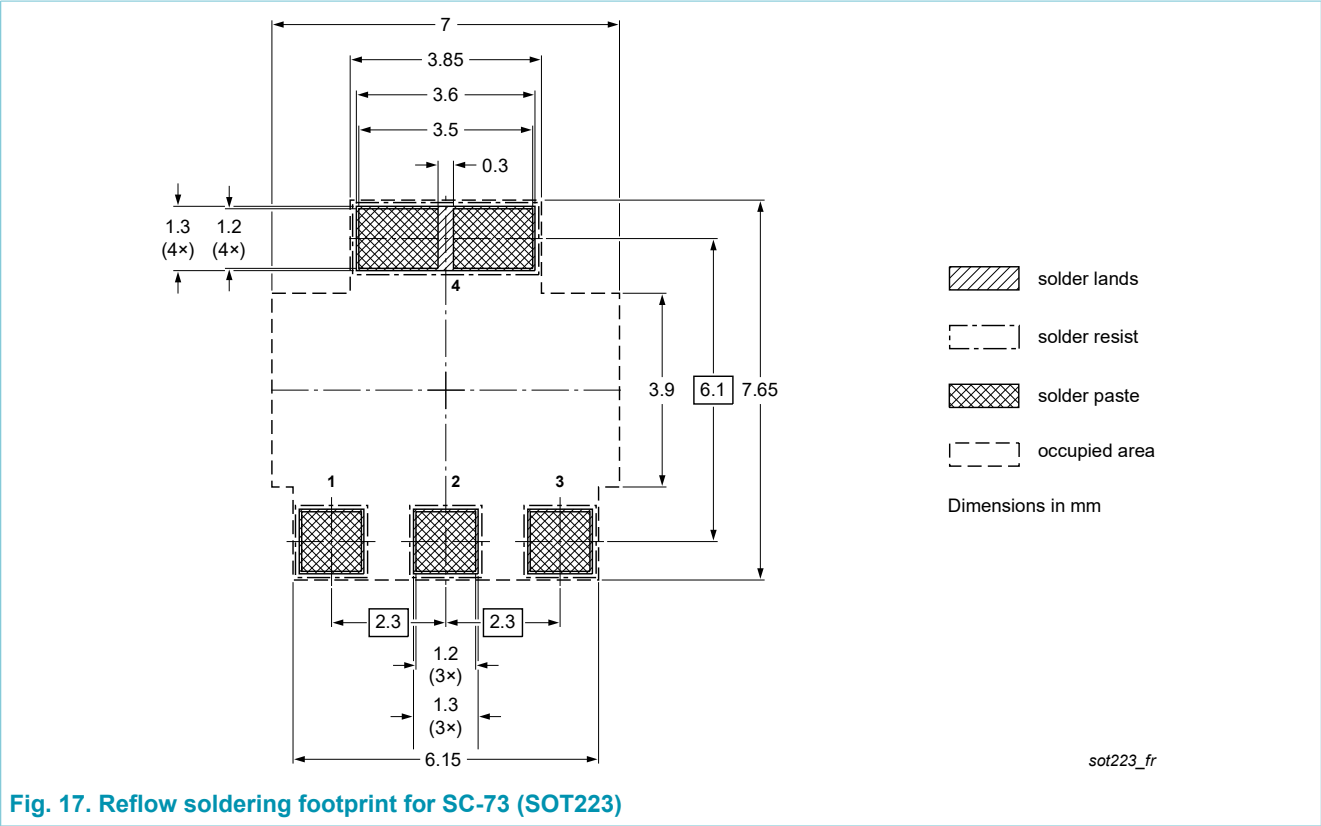
10. Package outline



11. Package outline (minimized)



12. Soldering



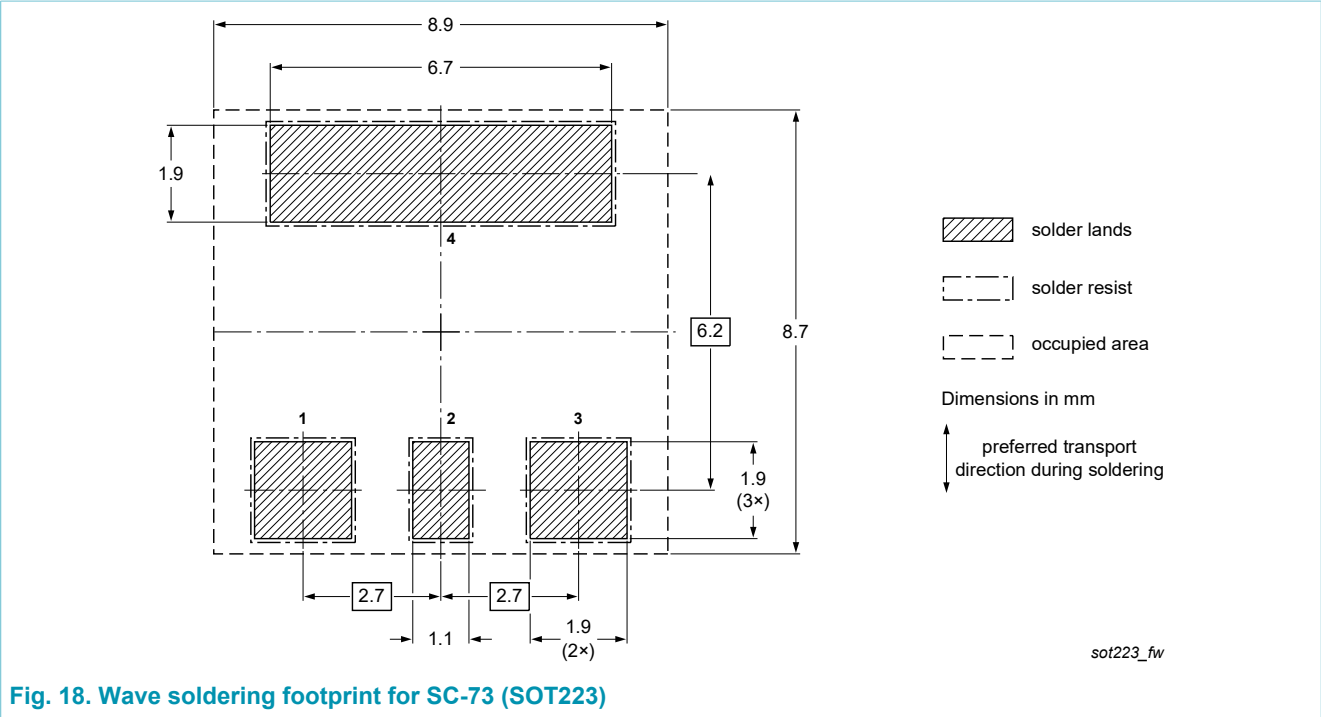


Fig. 18. Wave soldering footprint for SC-73 (SOT223)

13. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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14. Contents

1. General description..... 1

2. Features and benefits..... 1

3. Applications..... 1

4. Quick reference data..... 1

5. Pinning information.....2

6. Ordering information.....2

7. Limiting values..... 3

8. Thermal characteristics..... 6

9. Characteristics.....8

10. Package outline..... 11

11. Package outline (minimized)..... 12

12. Soldering..... 12

13. Legal information..... 14

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Date of release: 15 June 2016



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